

FIG. 1A

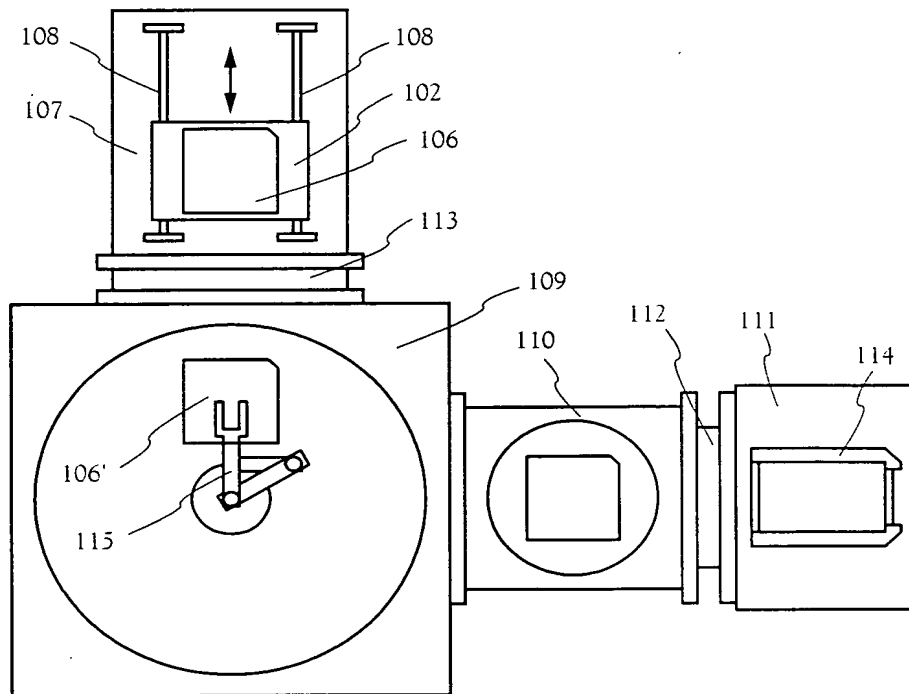
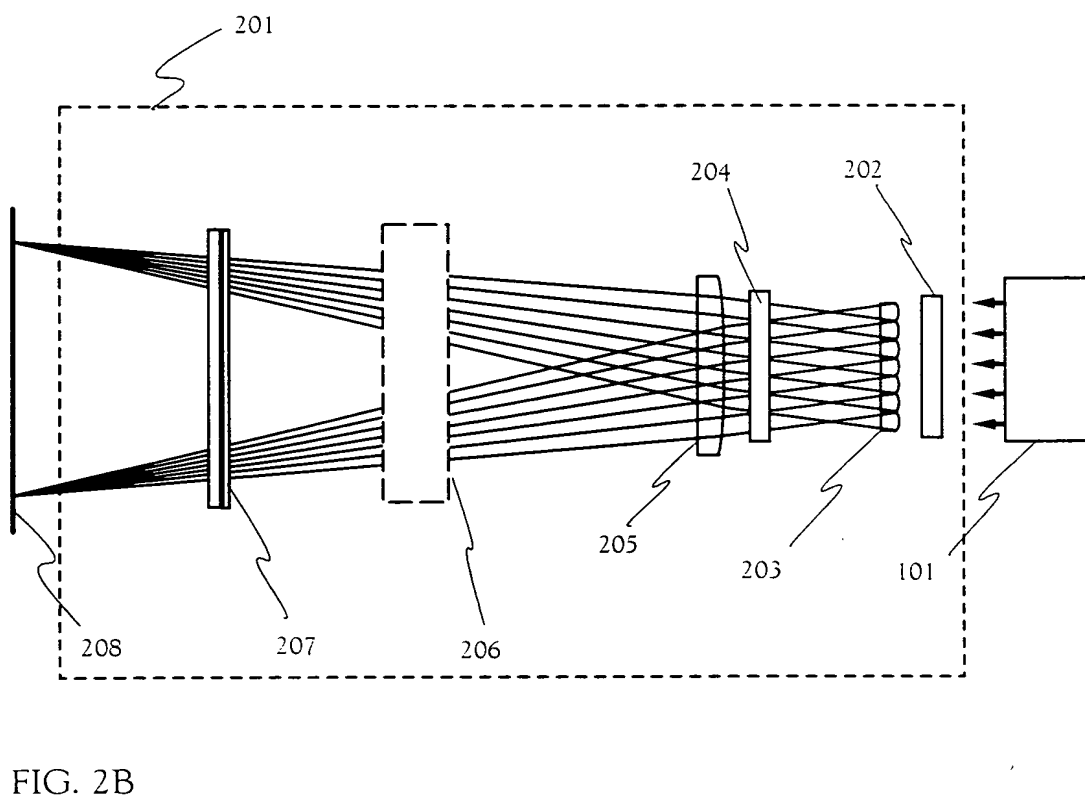
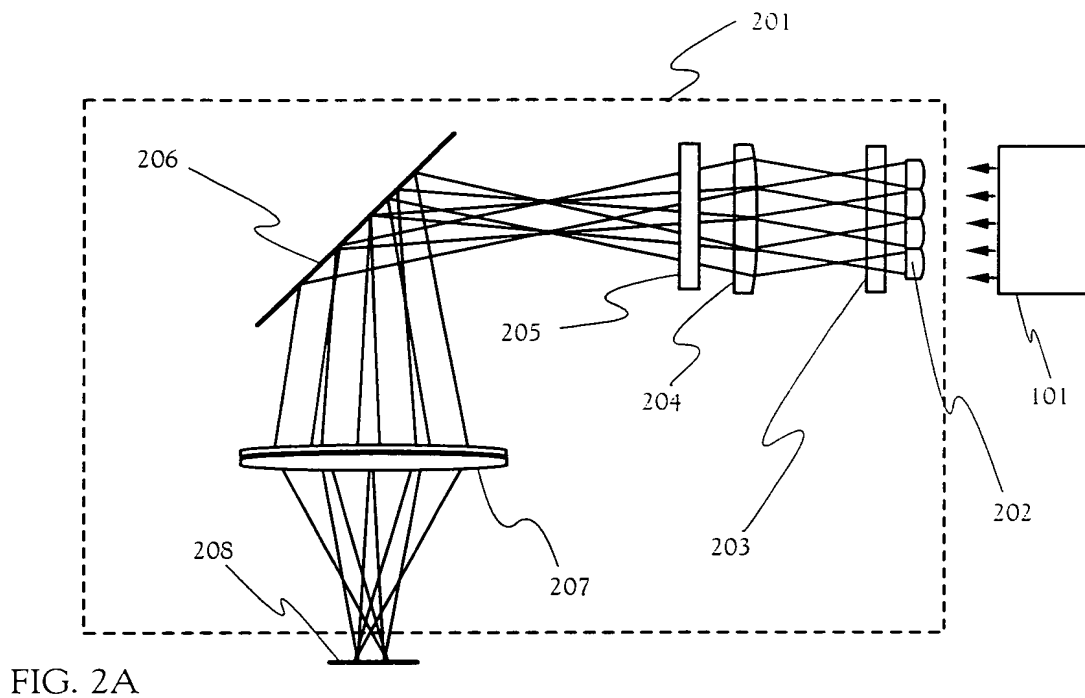


FIG. 1B



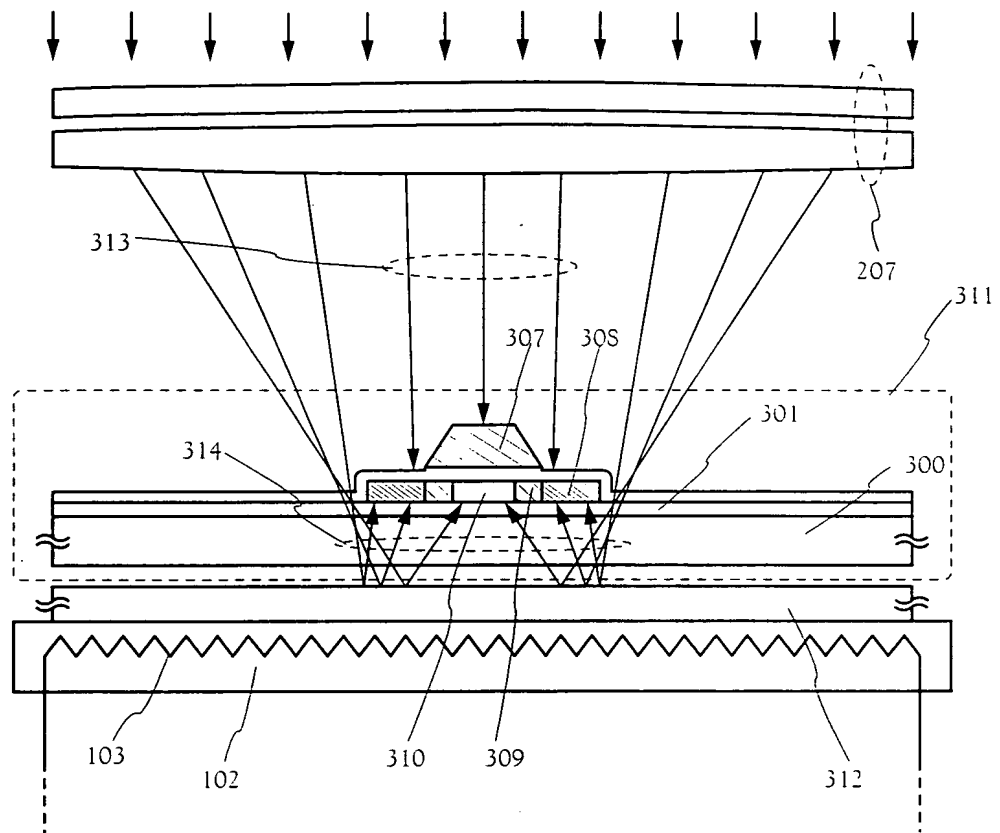


FIG. 3

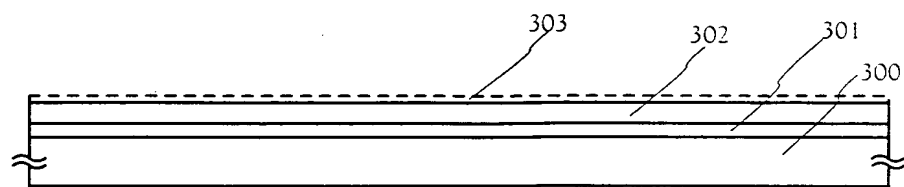


FIG. 4A

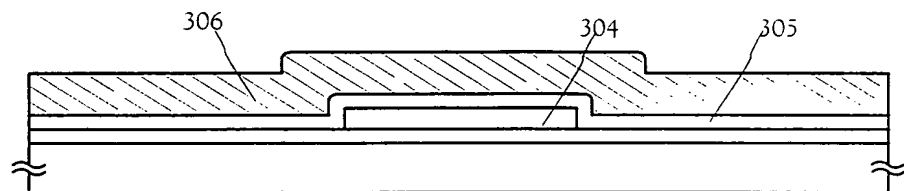


FIG. 4B

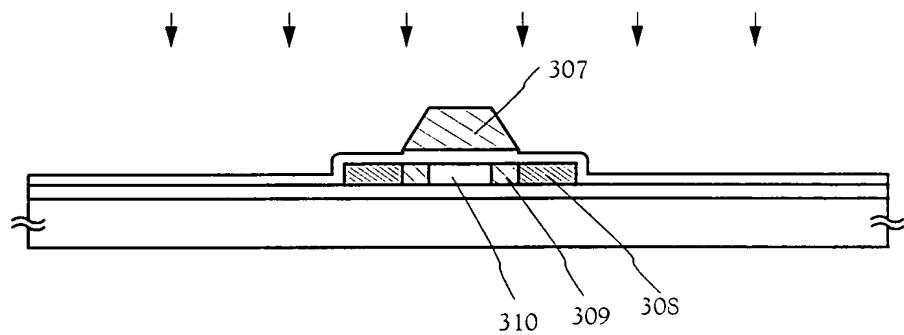


FIG. 4C

FIG. 5

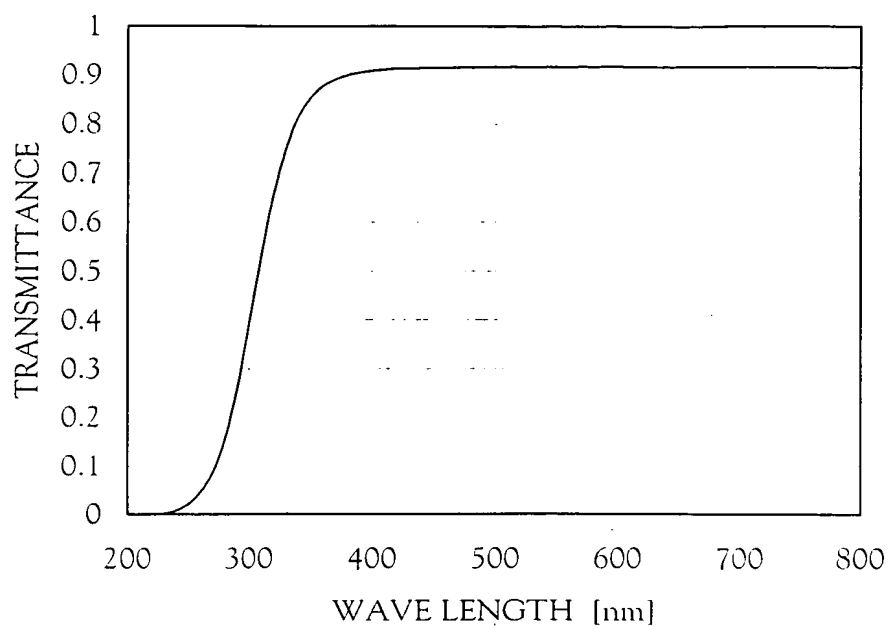


FIG. 6A

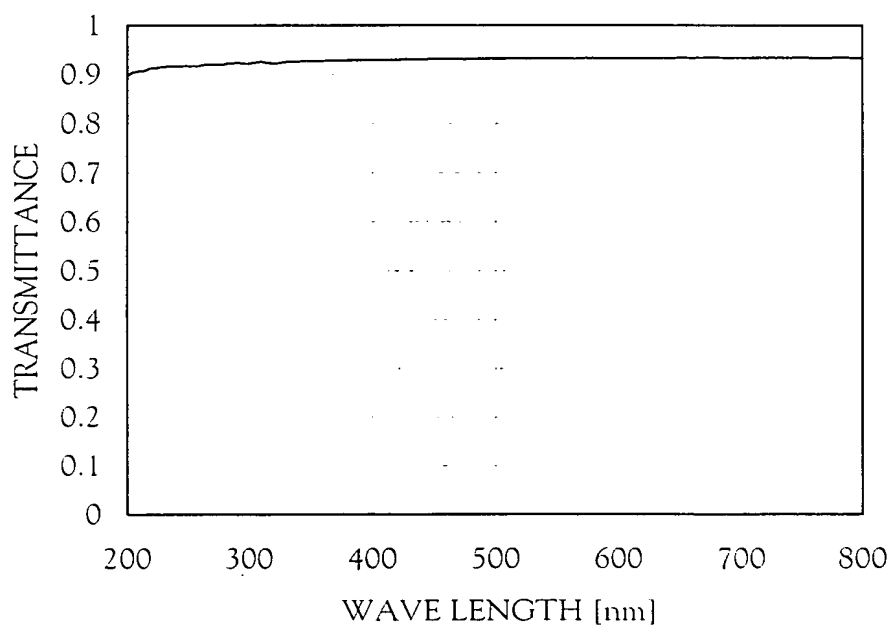


FIG. 6B

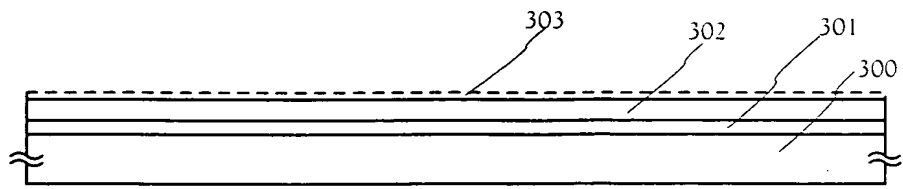


FIG. 7A

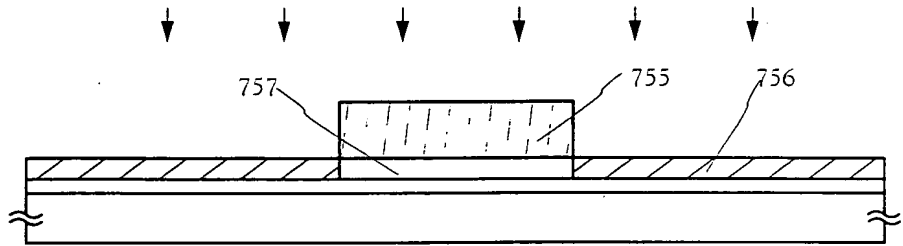


FIG. 7B

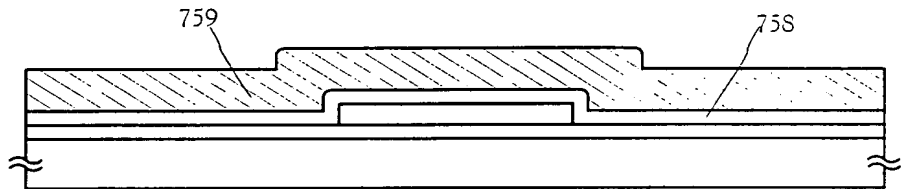


FIG. 7C

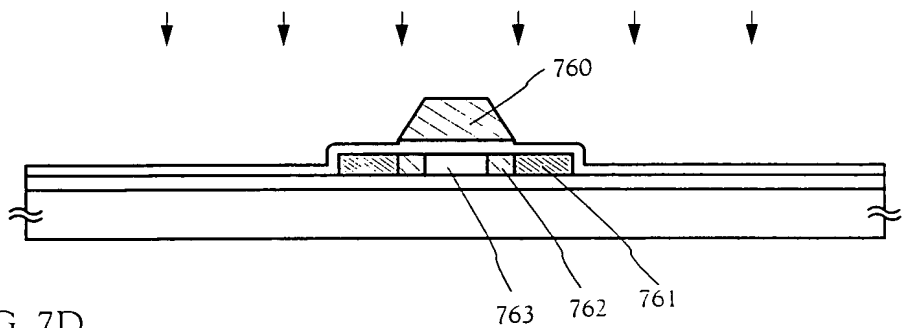


FIG. 7D

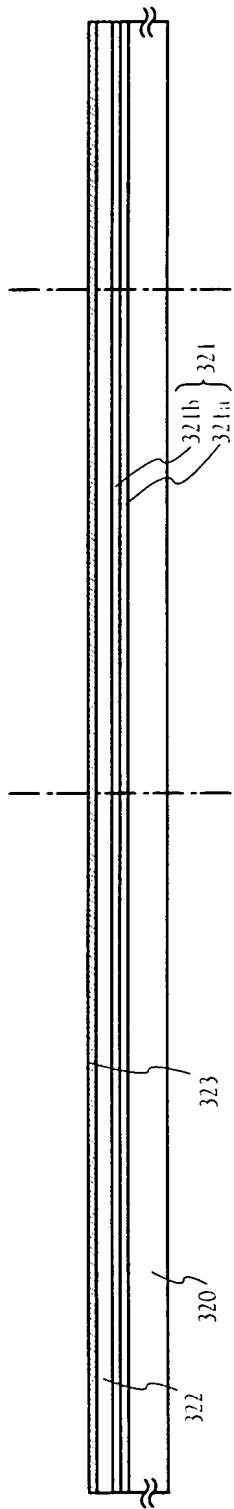


FIG. 8A

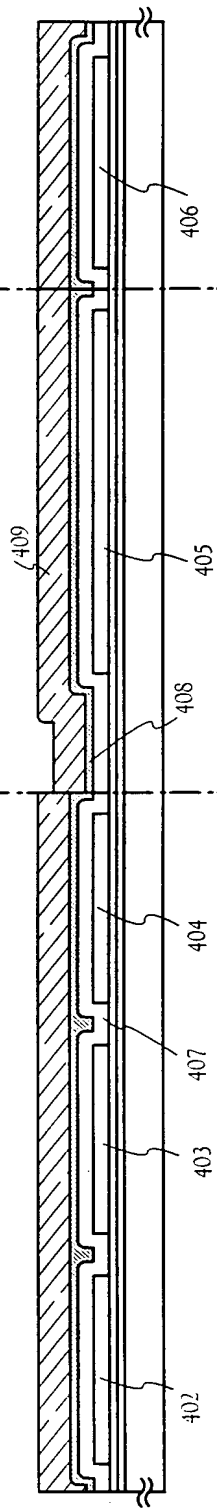


FIG. 8B

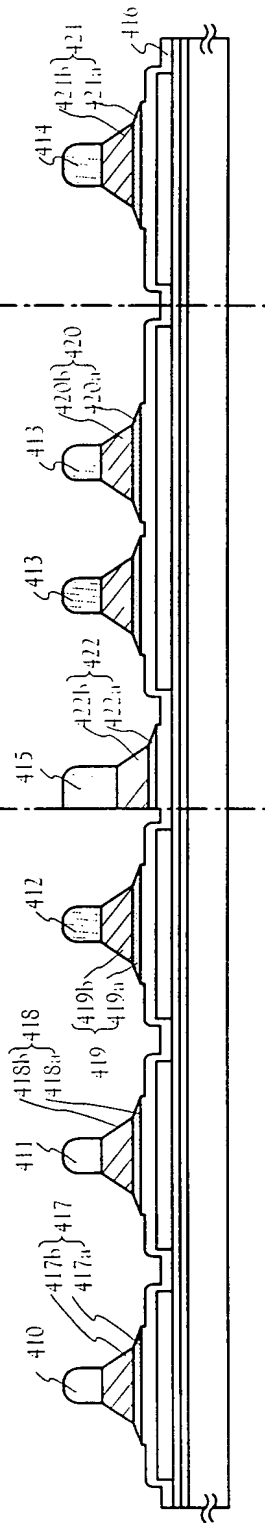


FIG. 8C

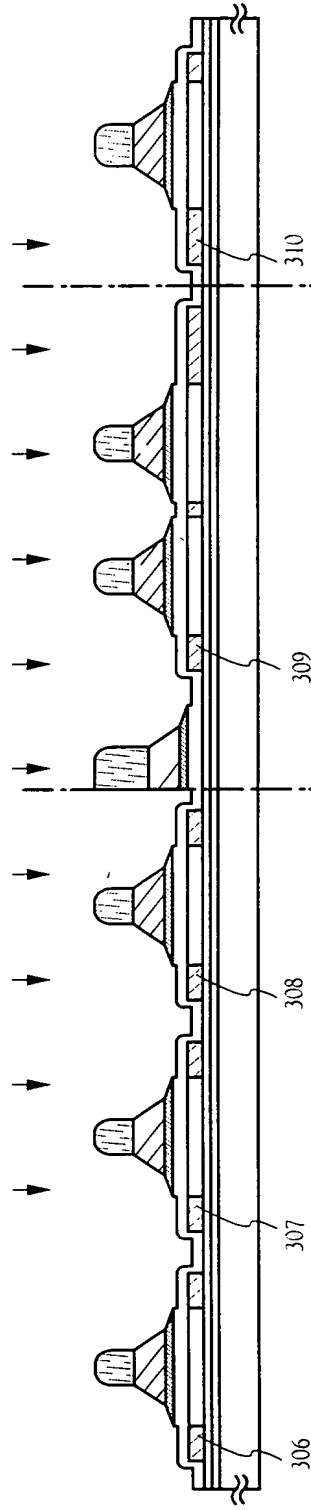


FIG. 9A

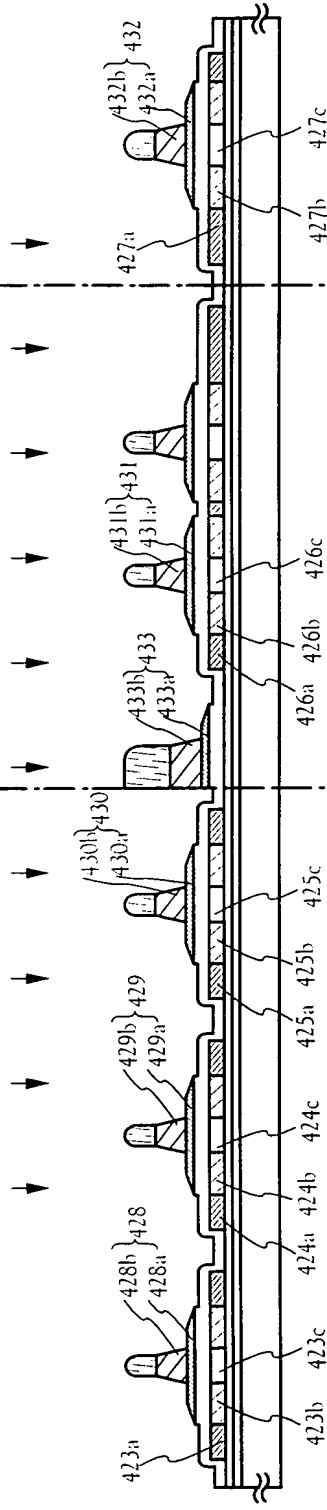


FIG. 9B

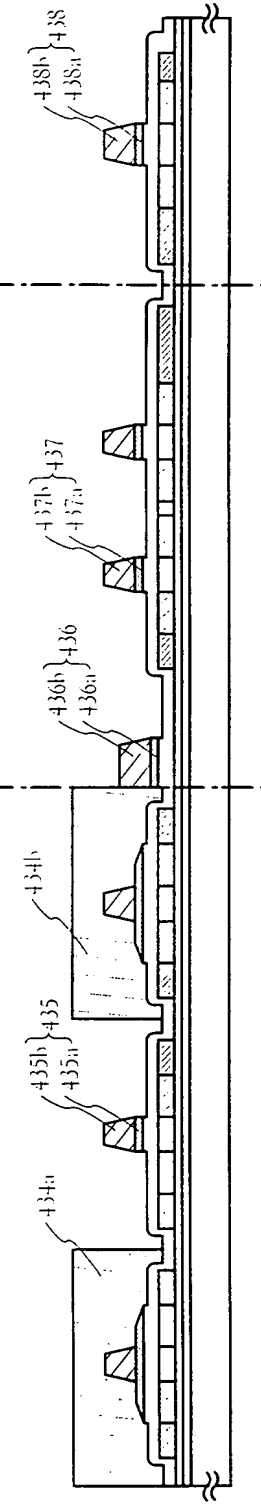


FIG. 9C

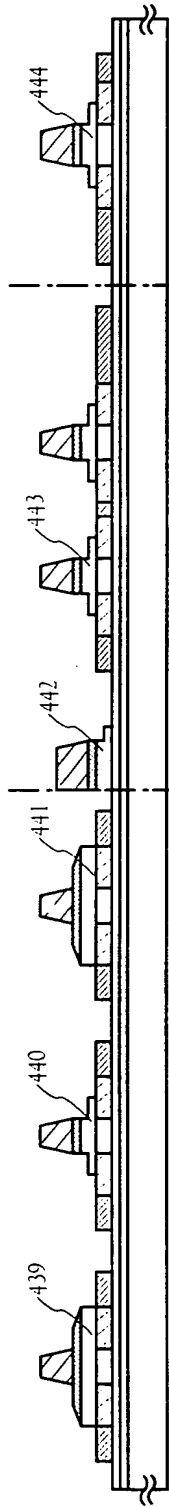


FIG. 10A

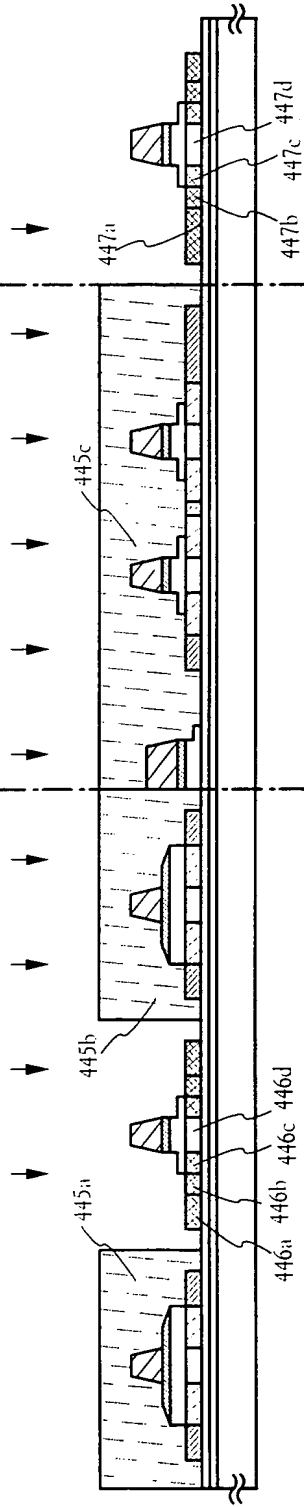


FIG. 10B

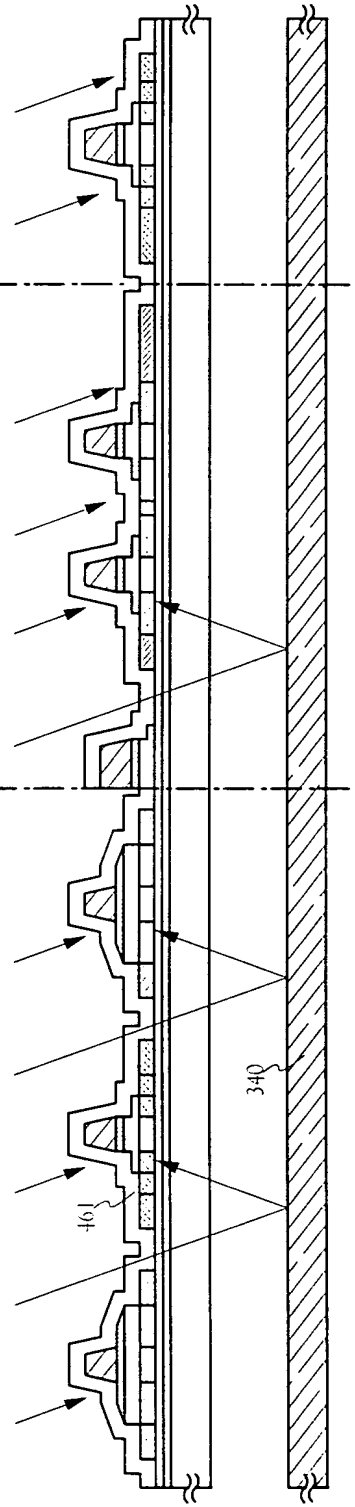


FIG. 10C

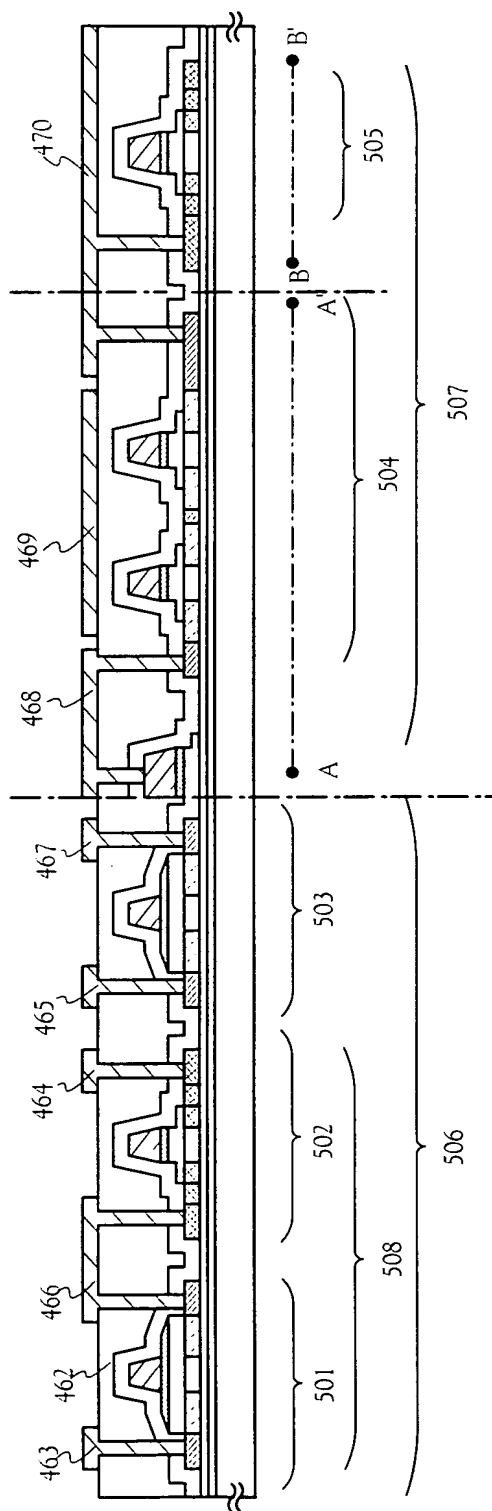


FIG. 11

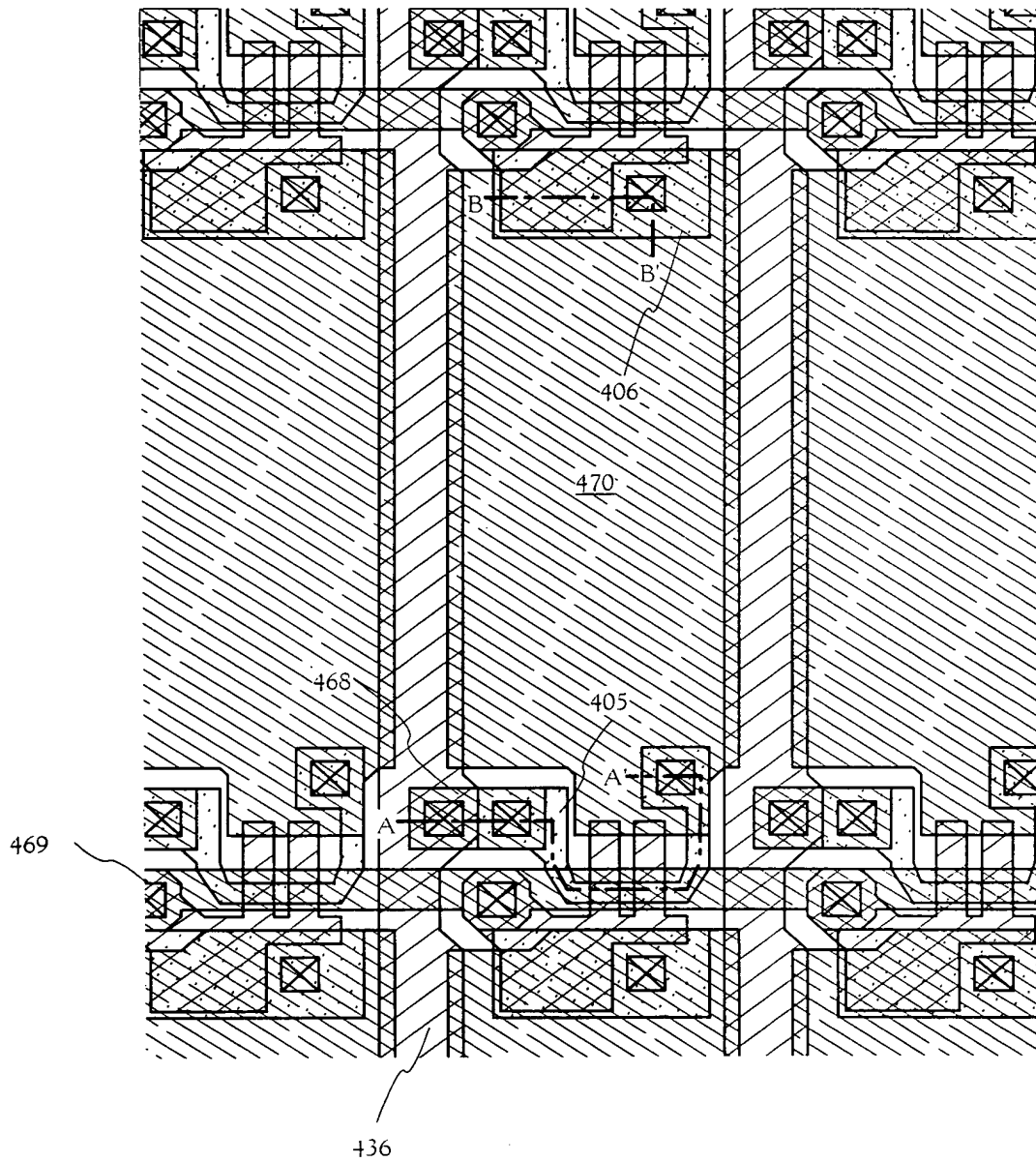


FIG. 12

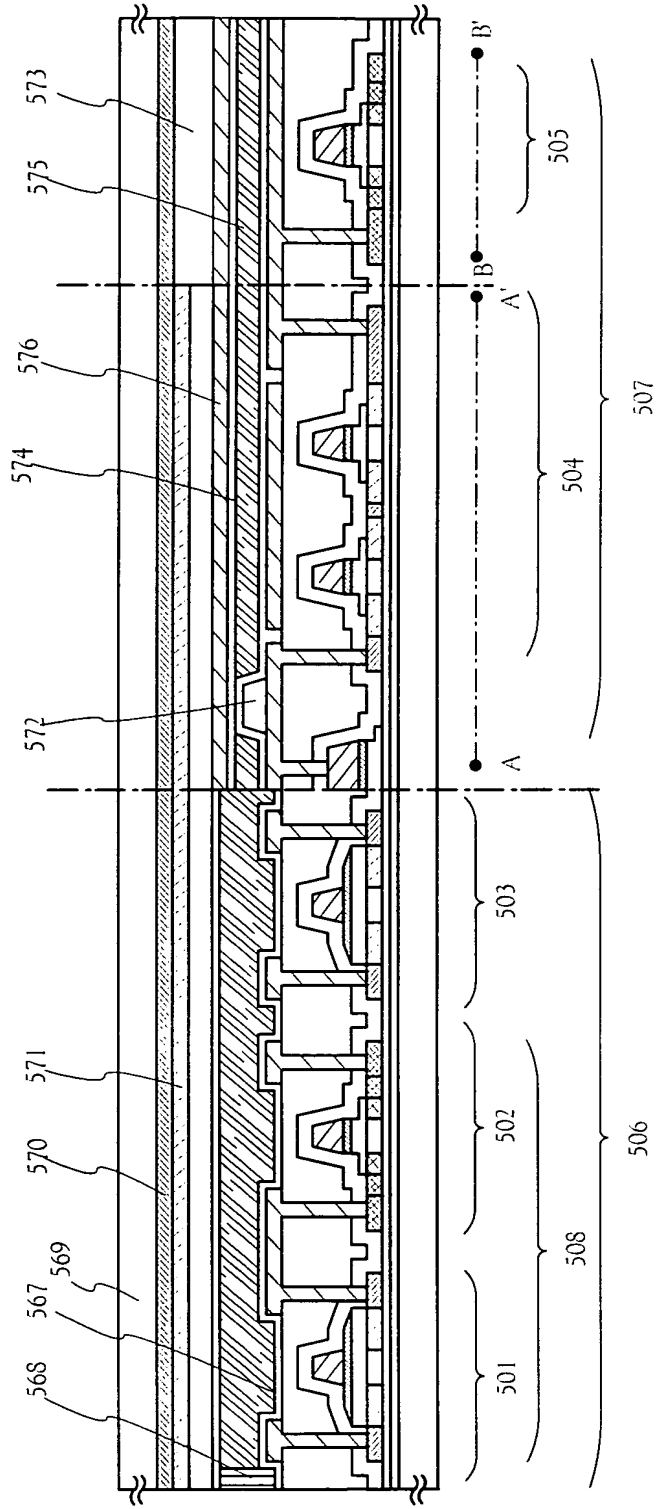


FIG. 13

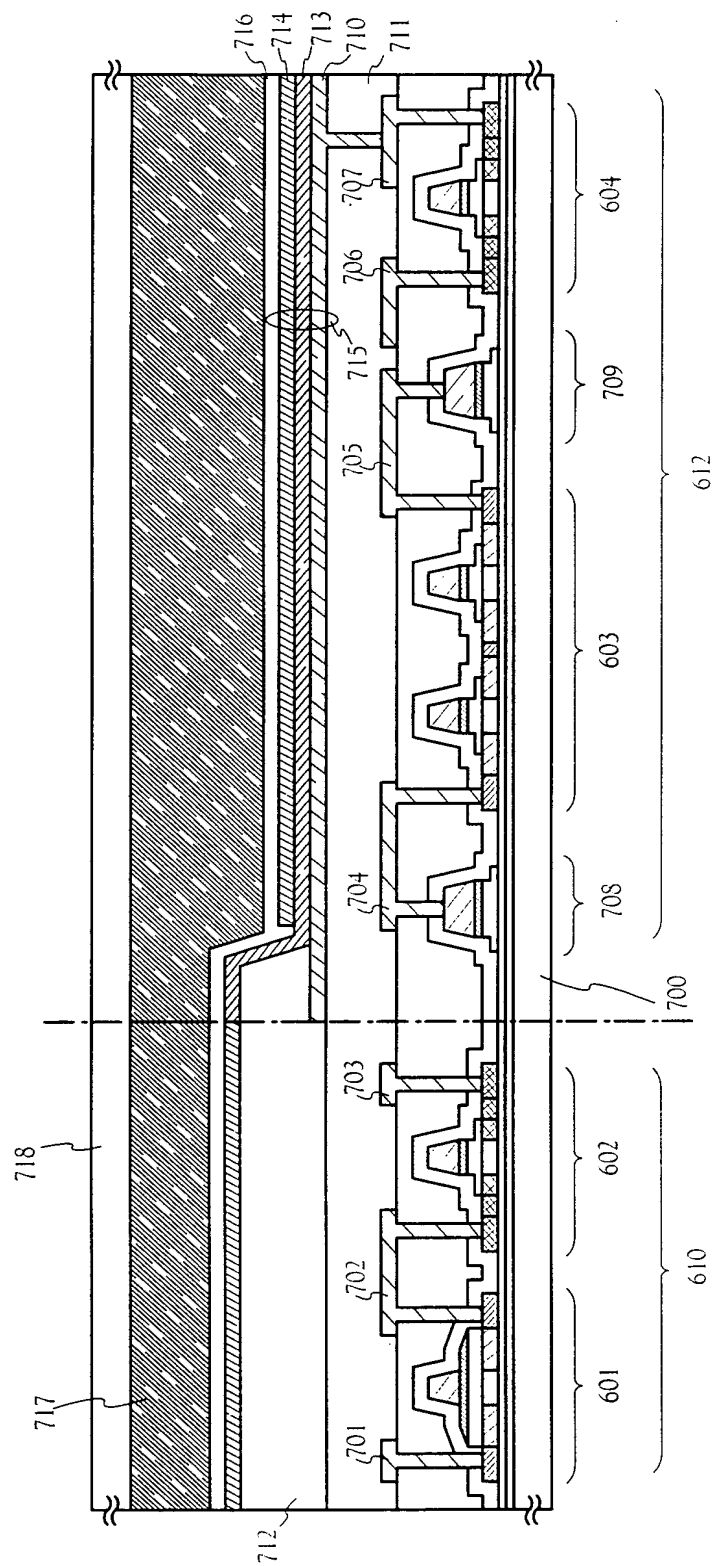


FIG. 14

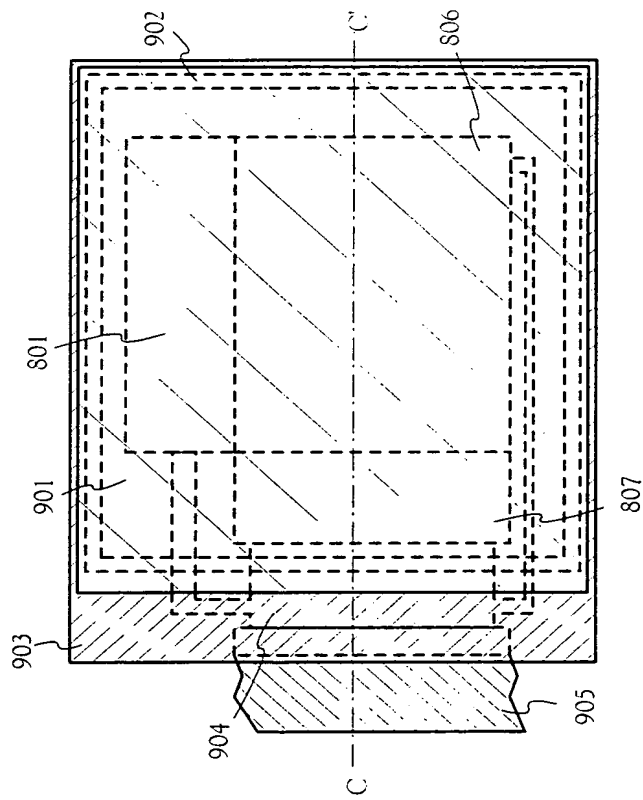


FIG. 15A

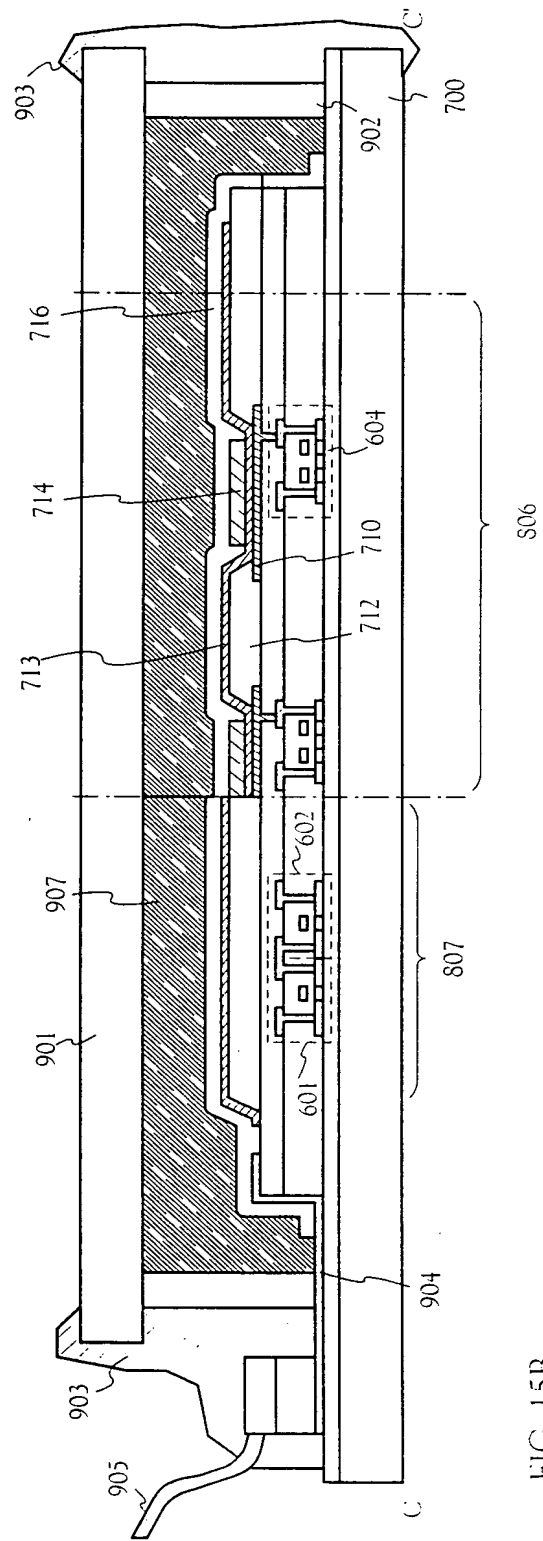


FIG. 15B

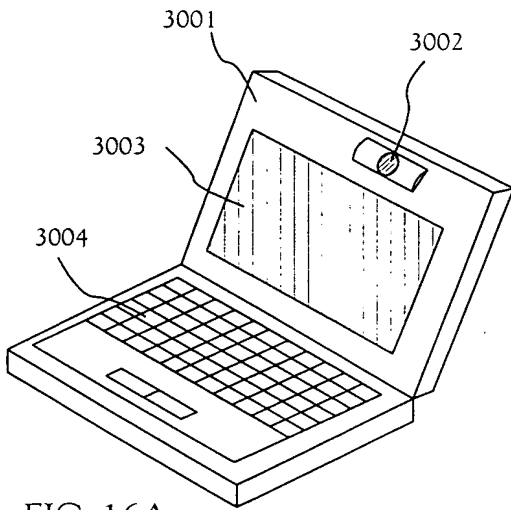


FIG. 16A

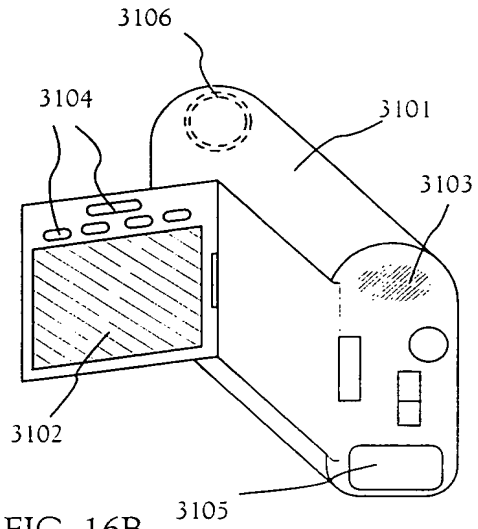


FIG. 16B

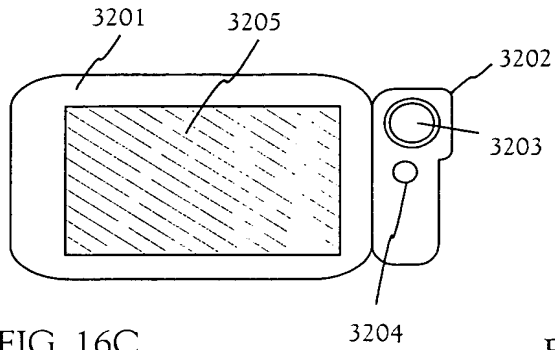


FIG. 16C

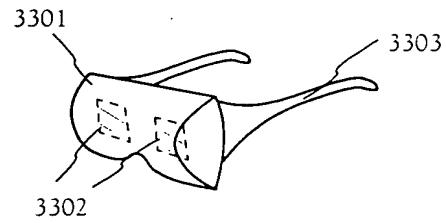


FIG. 16D

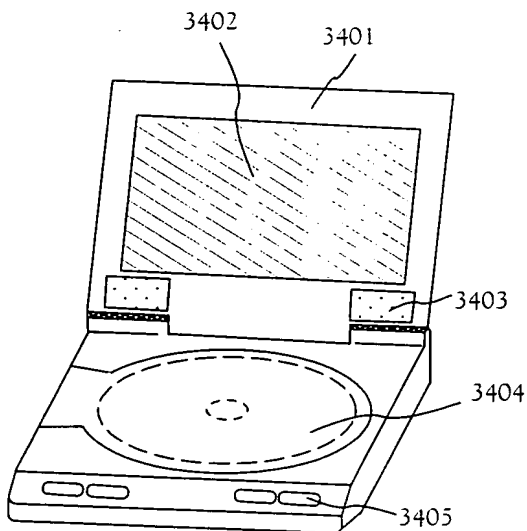


FIG. 16E

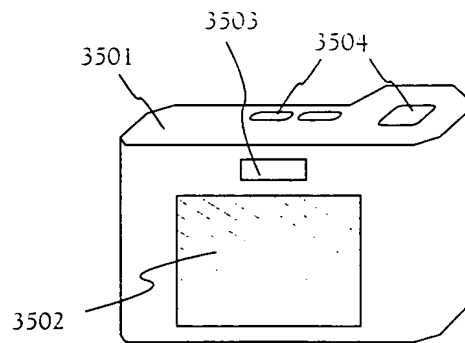


FIG. 16F

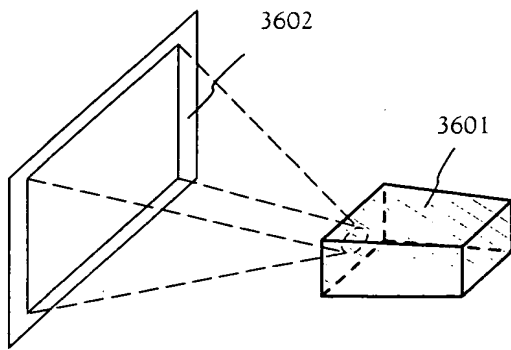


FIG. 17A

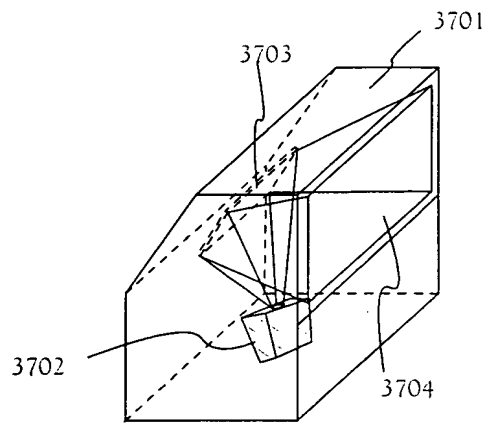


FIG. 17B

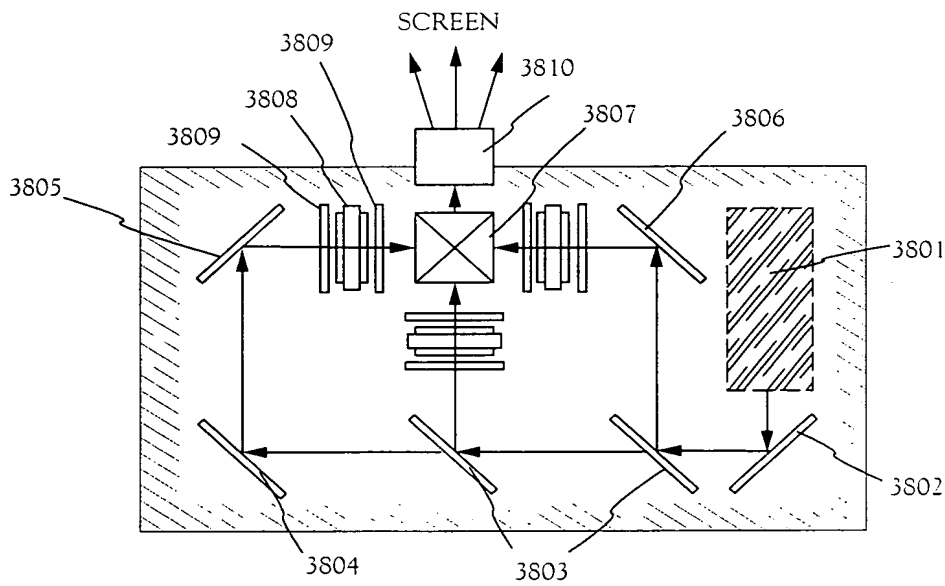


FIG. 17C

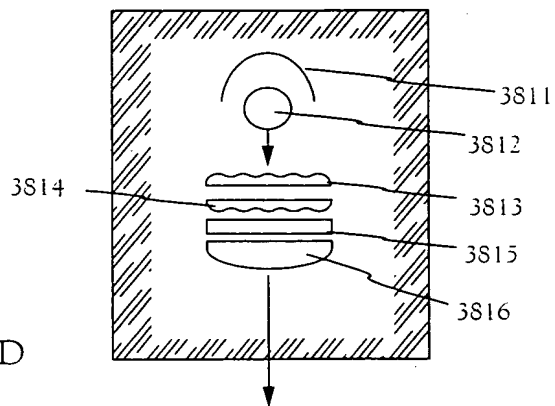


FIG. 17D

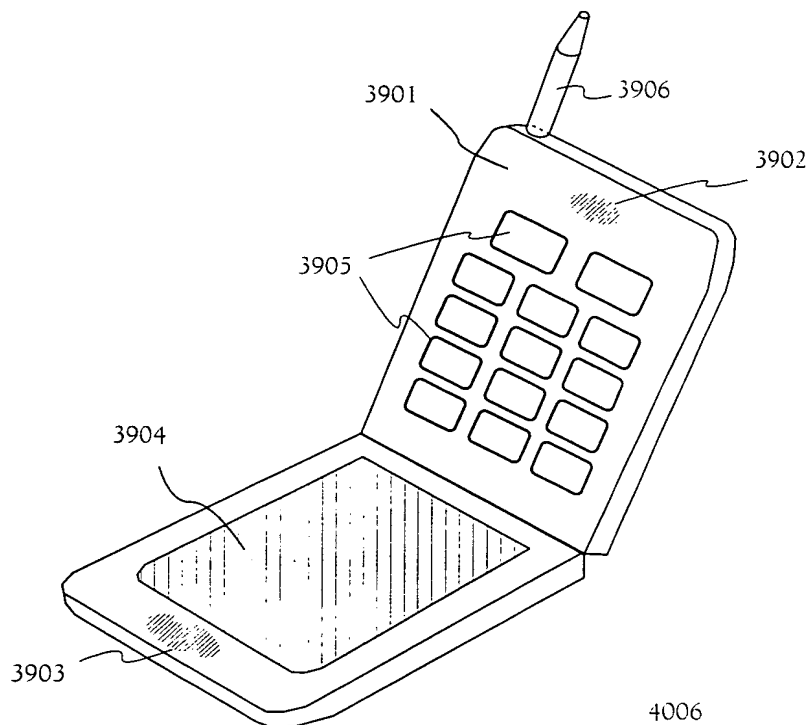


FIG. 18A

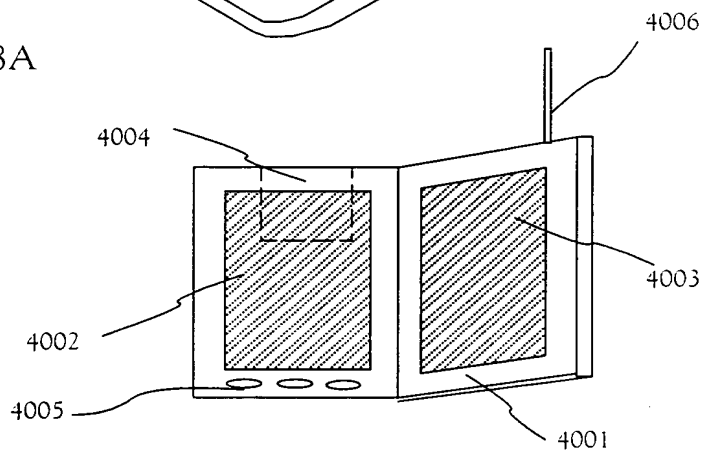


FIG. 18B

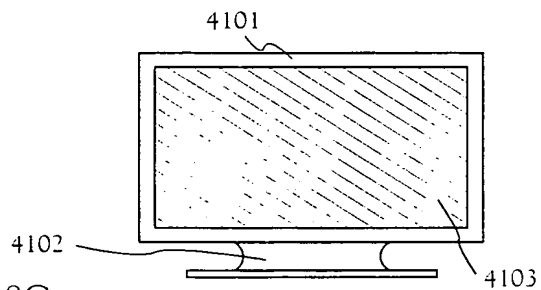


FIG. 18C

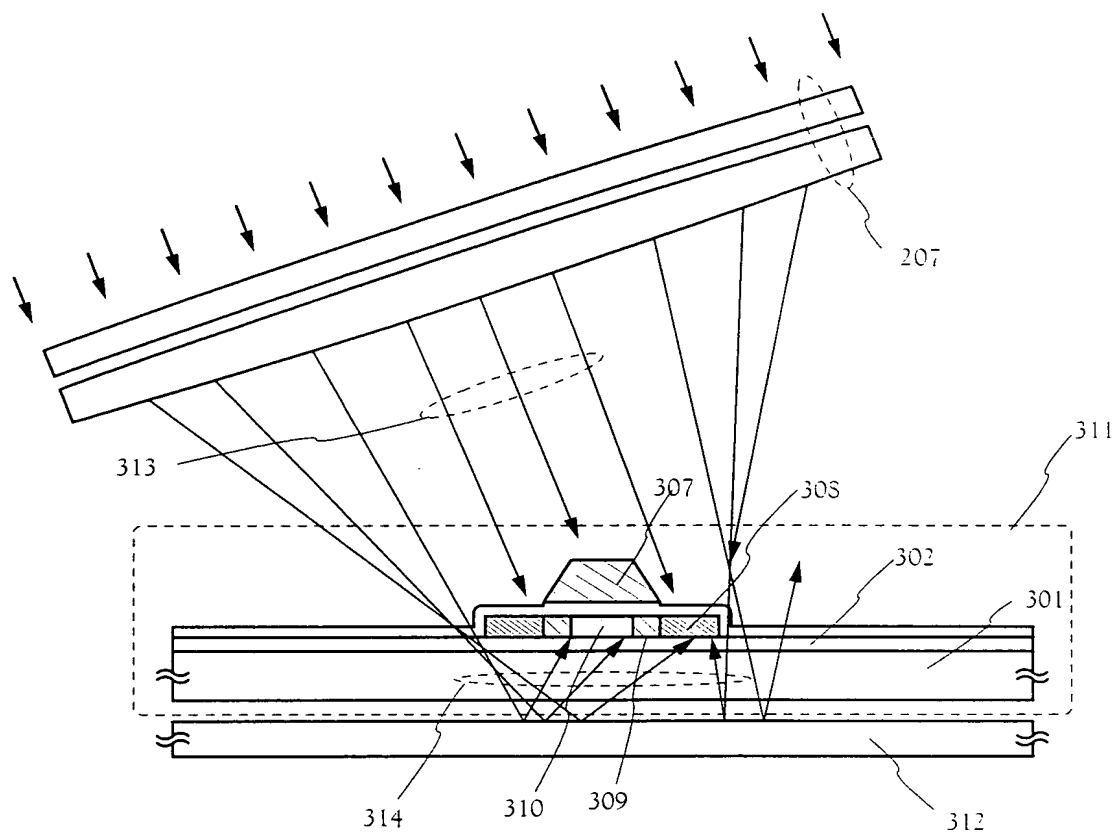


FIG. 19

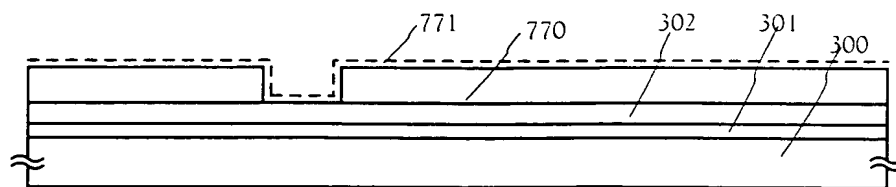


FIG. 20A

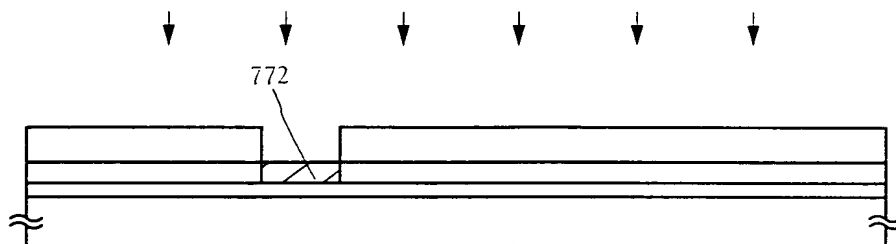


FIG. 20B

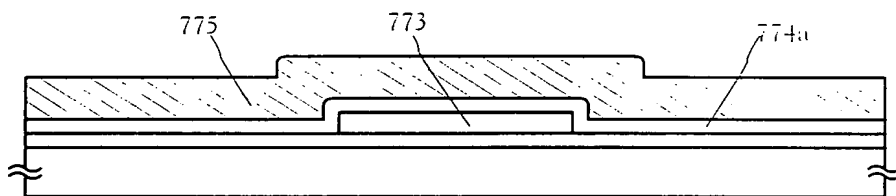


FIG. 20C

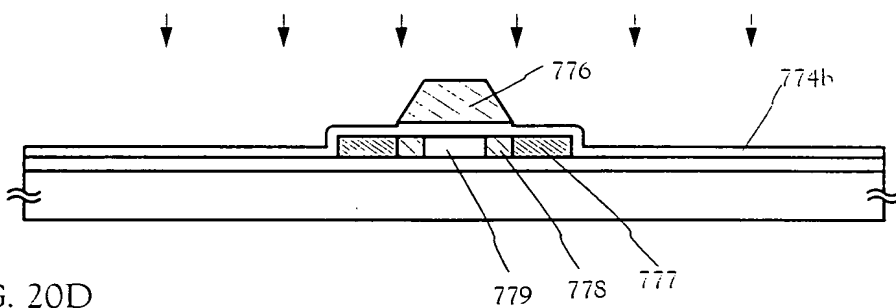


FIG. 20D

FIG. 21

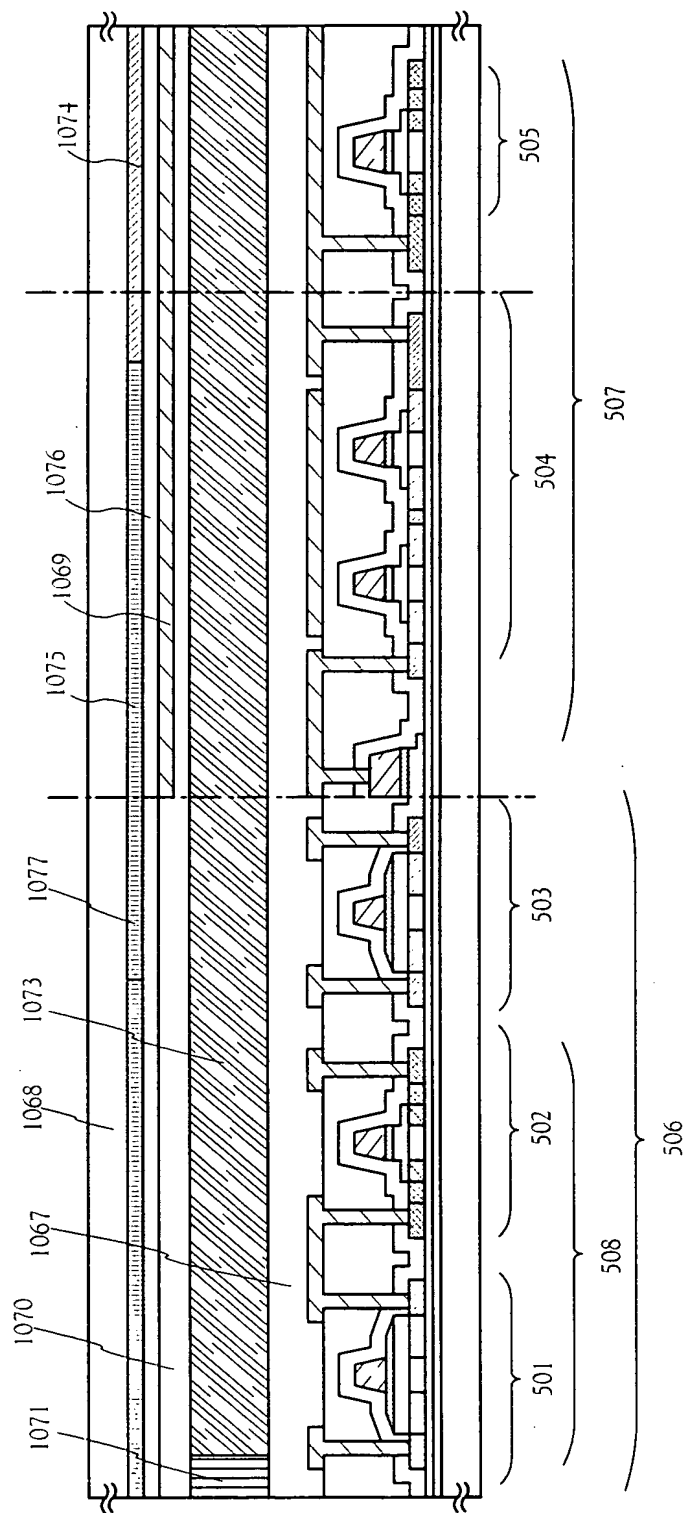


FIG. 21

LIGHT EMITTING DIRECTION

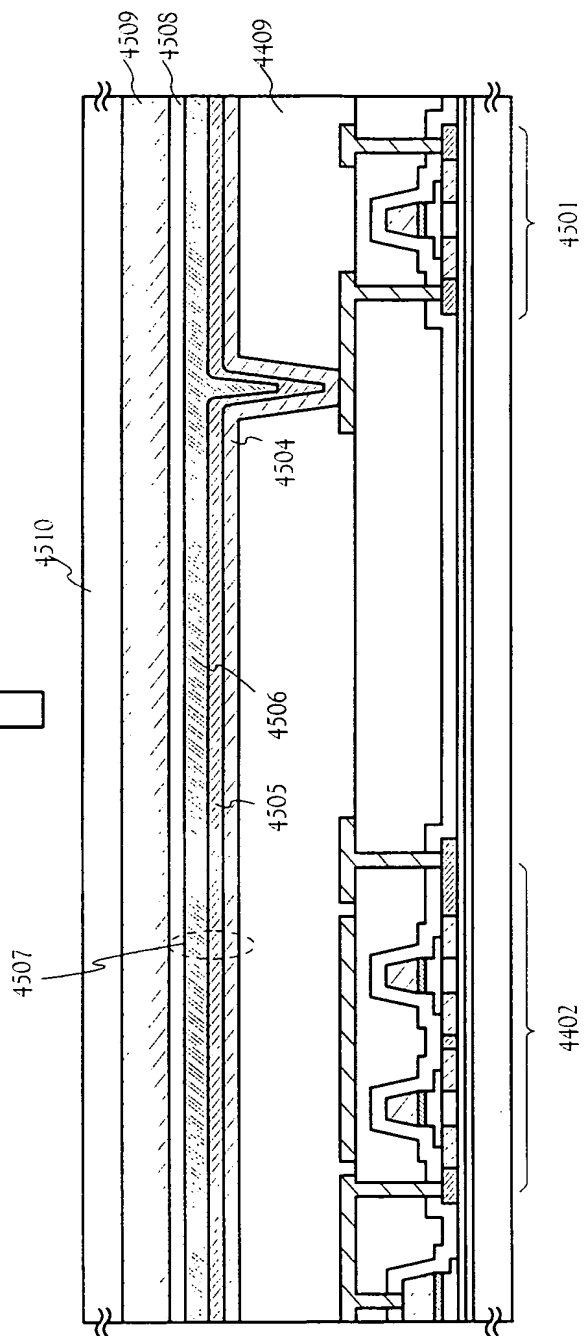
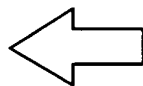


FIG. 22

A cross-sectional view of a semiconductor device. A central block 784 is positioned on a substrate 785. A layer 786 is located between the block 784 and the substrate 785. Arrows indicate downward force or pressure applied to the top surface of the block 784.

FIG. 23D